Electronic structure of defects and band gap engineering in RAIO₃ (R = Y, La, Gd, Yb, Lu) perovskites

Yu. Hizhnyi^{1,2*}, S.G. Nedilko¹, Ya. Zhydachevskyy^{2,3}, I. Kudrjavtseva⁴, V. Pankratov⁵, V. Stasiv², L. Vasylechko³, A. Lushchik⁴, M. Berkowski², A. Suchocki²

¹Taras Shevchenko National University of Kyiv, 64/13 Volodymyrska st., Kyiv 01033, Ukraine
 ²Institute of Physics, Polish Academy of Sciences, Al. Lotników 32/46, Warsaw 02-668, Poland
 ³ Lviv Polytechnic National University, 12 Bandera, Lviv 79013, Ukraine
 ⁴Institute of Physics, University of Tartu, W. Ostwaldi 1, Tartu 50411, Estonia
 ⁵Institute of Solid State Physics, University of Latvia, 8 Kengaraga st., Riga LV-1063, Latvia
 * e-mail of corresponding author: <u>hizhnyi@univ.kiev.ua</u>

Tuning of the charge trapping properties of oxide crystals via changing of their band-gap widths by cationic substitution is a promising approach in elaboration of efficient optical and scintillation materials [1, 2]. The main idea of this approach is that such substitution in oxide crystal may change its band gap and, consequently, the energy levels of defects states can change their depth with respect to the band edges. The band-gap engineering effect has been experimentally evidenced for several classes of oxide compounds. However specific electronic-level mechanisms which govern this effect in a particular crystal still remain unknown. The present work reveals such mechanisms in the case of YAlO₃ perovskite crystals in which Y cations are substituted with La.

The DFT-based theoretical calculations with use of the Plane-Wave Pseudopotential method were carried out in order to determine the influence of La doping on the energy positions defect levels in the crystals bandgap of YAlO₃. The geometry-optimized calculations were performed in the super-cell approach. The super-cells were constructed as 2x2x2 multiplication of the unit cell and comprised 160 atoms of YAlO₃ crystal. Several kinds of point defects and defect combinations were modeled in the super-cells: natural vacancies and vacancy complexes, interstitial oxygen defects and combinations of such interstitials with natural vacancies, cationic antisites, iso- and aliovalent cationic substitutions, as well as several other combinations of such defects in $Y_{0.75}La_{0.25}AlO_3$ mixed-cationic solid solution.

Results obtained in the calculations are compared with corresponding experimental data on the optical absorption in the VUV-UV range, luminescence spectroscopy under synchrotron radiation excitation, thermally stimulated luminescence (TSL) in 300 - 500 °C temperature range are carried out for the specially grown set of RAlO₃ (R = Y, La, Gd, Yb, Lu) single crystals and solid solutions.

The mechanisms of formation of TSL glow peaks of (Y,Gd,La)AlO₃:Mn⁴⁺ crystals are discussed using the obtained computational results. The origin of traps, which form the TSL glow peaks of YAlO₃ crystals above room temperature, is revealed.

References

[1] I.V. Vrubel, et al., *Crystal Growth and Design*, 17 (2017) 1863-1869
[2] M. Fasoli, et al. *Physical Review B*, 84 (2011) 081102(R)

Acknowledgments

The work was supported by the Polish National Science Centre (project no. 2018/31/B/ST8/00774), by the NATO SPS Project G5647, and by the National Research Foundation of Ukraine (grant 2020.01/0248).